



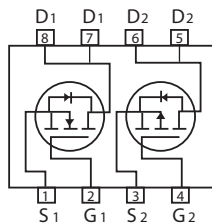
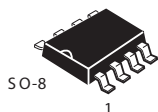
Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT SUMMARY (N-Channel)

V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
40V	5A	35 @ V _{GS} = 10V
		60 @ V _{GS} = 4.5V

PRODUCT SUMMARY (P-Channel)

V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
-40V	-4A	45 @ V _{GS} = -10V
		60 @ V _{GS} = -4.5V



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	40	-40	V
Gate-Source Voltage		V _{GS}	±20	± 20	V
Drain Current-Continuous ^a @ T _a	25°C	I _D	5	-4	A
	70°C		4.2	-3.4	A
-Pulsed ^b		I _{DM}	20	-16	A
Drain-Source Diode Forward Current ^a		I _S	1.7	-1.7	A
Maximum Power Dissipation ^a	T _a = 25°C	P _D	2		W
	T _a =70°C		1.44		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θ JA	62.5	°C/W
--	---------------	------	------

STM8450

N-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 32V, V _{GS} = 0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250uA	1.0	2.0	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5A		25	35	m ohm
		V _{GS} = 4.5V, I _D = 4A		50	60	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	15			A
Forward Transconductance	g _{FS}	V _{DS} = 5V, I _D = 5A		8		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz		910	995	pF
Output Capacitance	C _{OSS}			130	150	pF
Reverse Transfer Capacitance	C _{RSS}			95	108	pF
Gate resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz		3		ohm
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 15V I _D = 3 A V _{GS} = 10V R _{GEN} = 4.7 ohm		17	19	ns
Rise Time	t _r			4.3	5	ns
Turn-Off Delay Time	t _{D(OFF)}			23.5	27	ns
Fall Time	t _f			9.5	11	ns
Total Gate Charge	Q _g	V _{DS} = 24V, I _D = 5A, V _{GS} = 10V		18.3	21	nC
		V _{DS} = 24V, I _D = 5A, V _{GS} = 4.5V		9	10	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 24V, I _D = 5 A V _{GS} = 4.5V		3.3	4	nC
Gate-Drain Charge	Q _{gd}			4.2	5	nC

STM8450

P-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -32V, V _{GS} = 0V			-1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250uA	-0.8	-1.5	-2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -4A		35	45	m ohm
		V _{GS} = -4.5V, I _D = -3A		50	60	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = -5V, V _{GS} = -10V	20			A
Forward Transconductance	g _{FS}	V _{DS} = -5V, I _D = -4A		8		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz		1128	1250	pF
Output Capacitance	C _{OSS}			182	210	pF
Reverse Transfer Capacitance	C _{RSS}			110	130	pF
Gate resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz		3.5		ohm
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = -15V I _D = -2.2A V _{GS} = -10V R _{GEN} = 4.7 ohm		17.3	20	ns
Rise Time	t _r			7	8	ns
Turn-Off Delay Time	t _{D(OFF)}			82	95	ns
Fall Time	t _f			27.6	32	ns
Total Gate Charge	Q _g	V _{DS} = -24V, I _D = -4A, V _{GS} = -10V		20.5	23	nC
		V _{DS} = -24V, I _D = -4A, V _{GS} = -4.5V		9.8	11	nC
Gate-Source Charge	Q _{gs}	V _{DS} = -24V, I _D = -4 A V _{GS} = -4.5V		2.8	3.2	nC
Gate-Drain Charge	Q _{gd}			3.9	4.5	nC

STM8450

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 1.7A	N-Ch	0.8	1.2	V
		V _{GS} = 0V, I _S = -1.7A	P-Ch	-0.77	-1.2	

Notes

- a.Surface Mounted on FR4 Board, t ≤ 10sec.
 - b.Pulse Test:Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 - c.Guaranteed by design, not subject to production testing.
- N-Channel

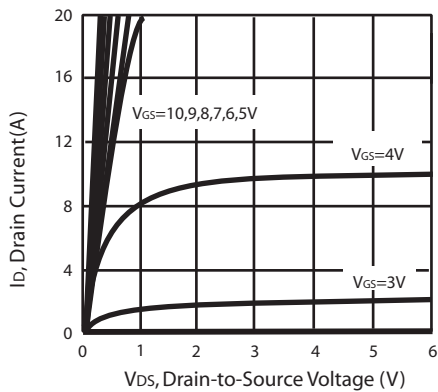


Figure 1. Output Characteristics

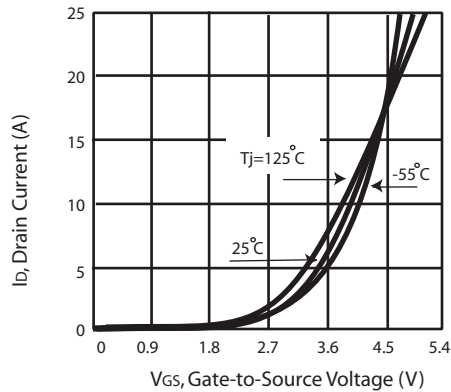


Figure 2. Transfer Characteristics

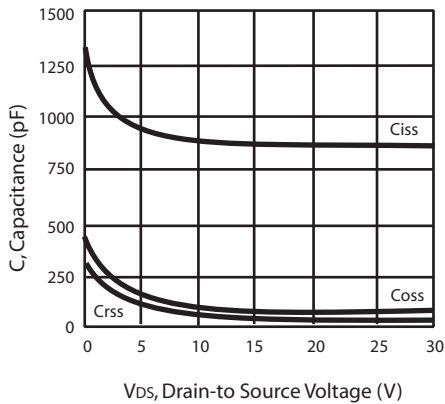


Figure 3. Capacitance

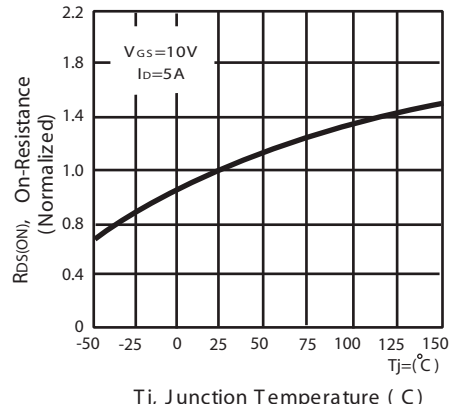


Figure 4. On-Resistance Variation with Drain Current and Temperature

STM8450

N-Channel

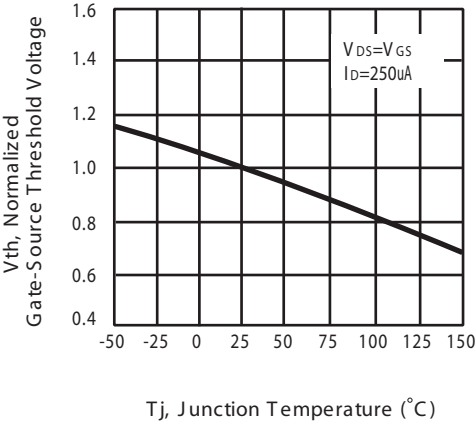


Figure 5. Gate Threshold Variation with Temperature

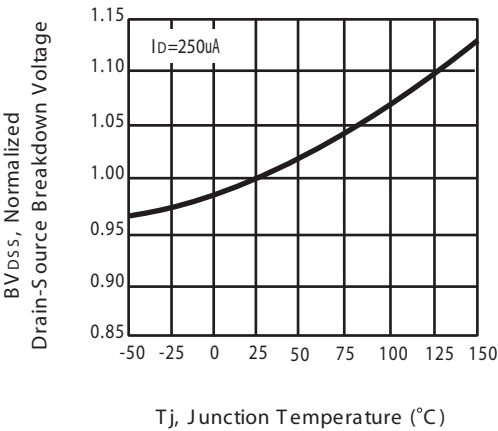


Figure 6. Breakdown Voltage Variation with Temperature

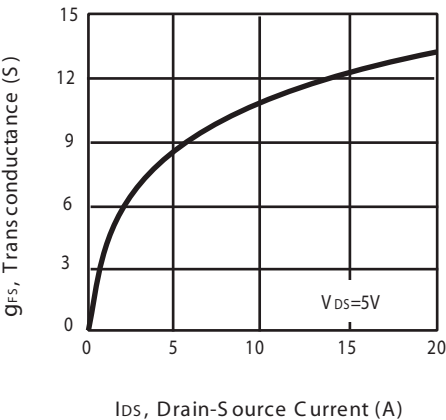


Figure 7. Transconductance Variation with Drain Current

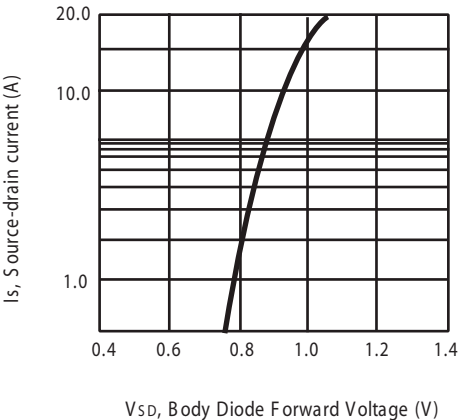


Figure 8. Body Diode Forward Voltage Variation with Source Current

STM8450

P-Channel

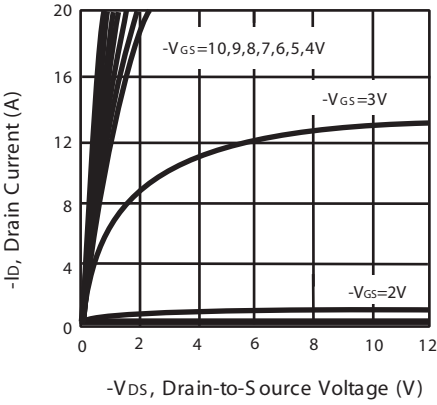


Figure 1. Output Characteristics

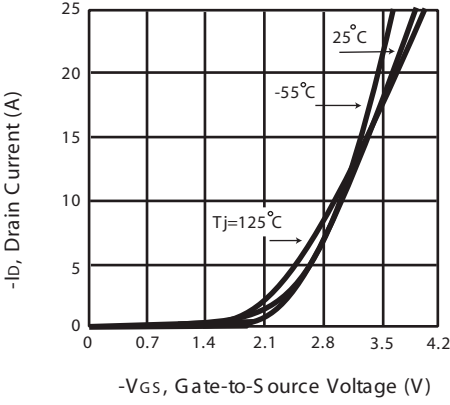


Figure 2. Transfer Characteristics

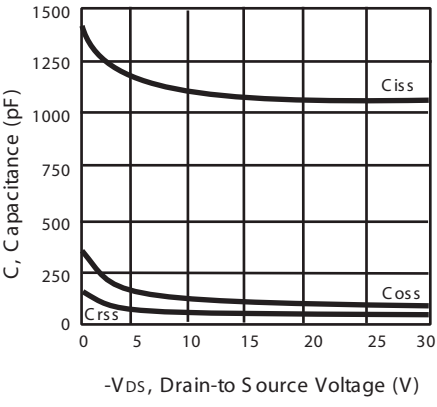


Figure 3. Capacitance

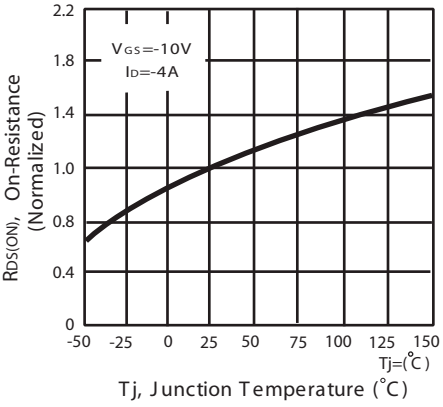


Figure 4. On-Resistance Variation with Temperature

STM8450

P-Channel

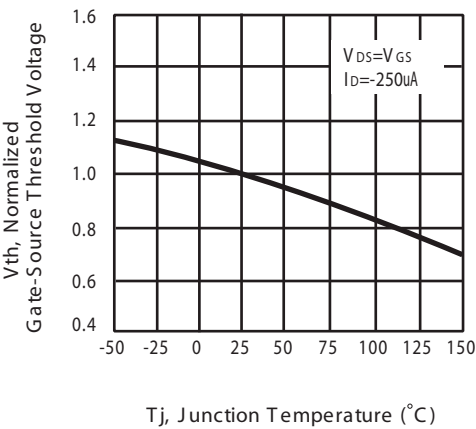


Figure 5. Gate Threshold Variation with Temperature

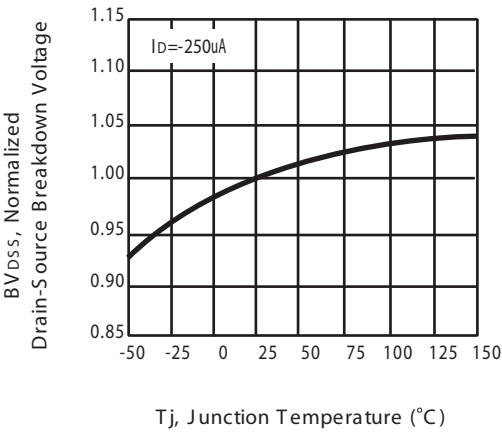


Figure 6. Breakdown Voltage Variation with Temperature

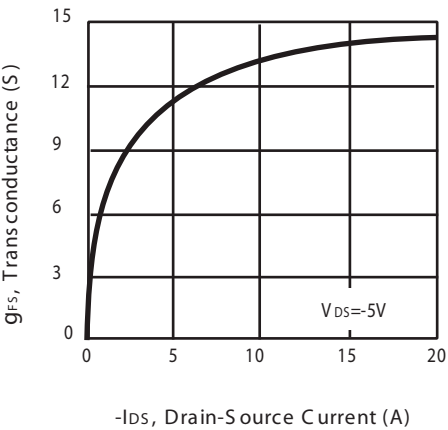


Figure 7. Transconductance Variation with Drain Current

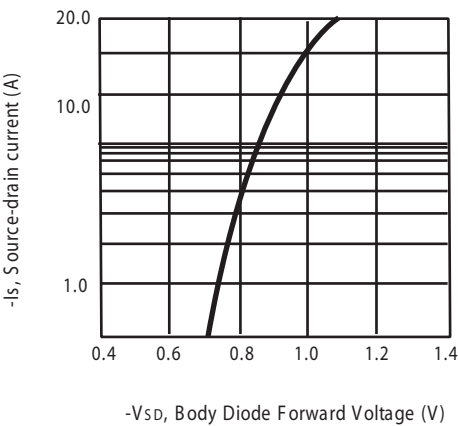
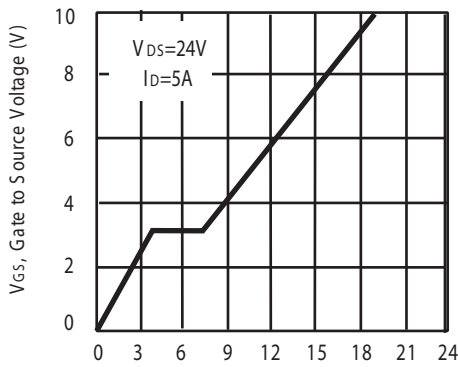


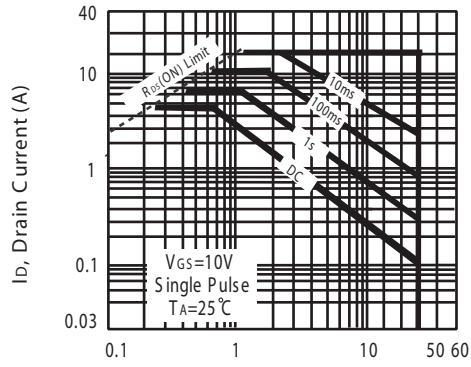
Figure 8. Body Diode Forward Voltage Variation with Source Current

STM8450

N-Channel

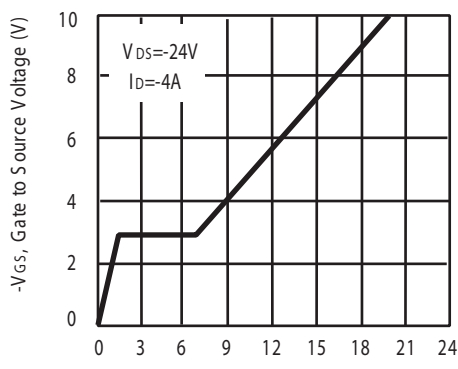


Qg, Total Gate Charge (nC)
Figure 9. Gate Charge

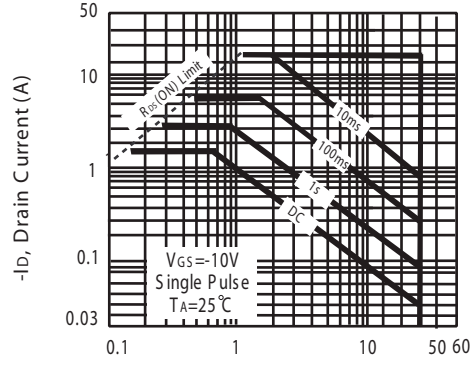


V_{DS} , Drain-Source Voltage (V)
Figure 10. Maximum Safe Operating Area

P-Channel



Qg, Total Gate Charge (nC)
Figure 9. Gate Charge



$-V_{DS}$, Body Diode Forward Voltage (V)
Figure 10. Maximum Safe Operating Area

STM8450

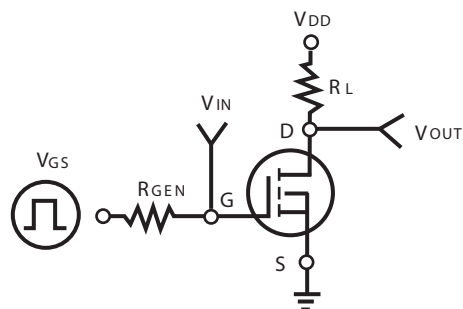


Figure 11. Switching Test Circuit

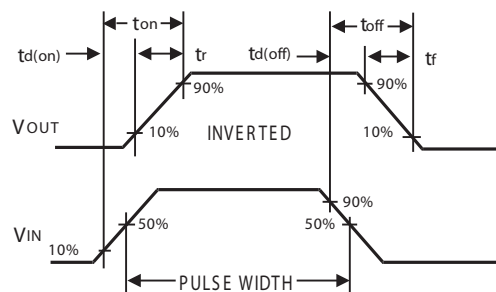
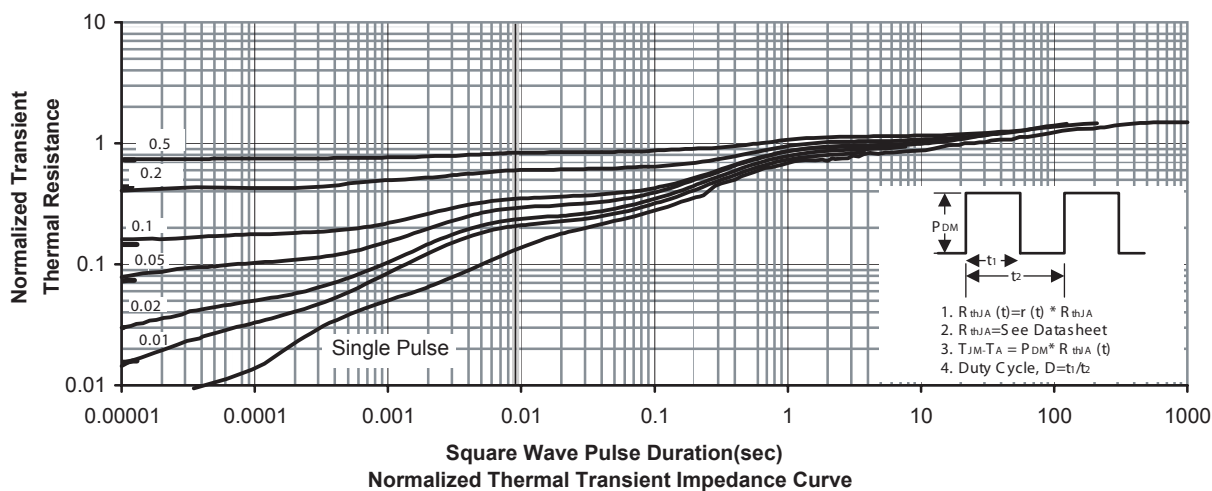
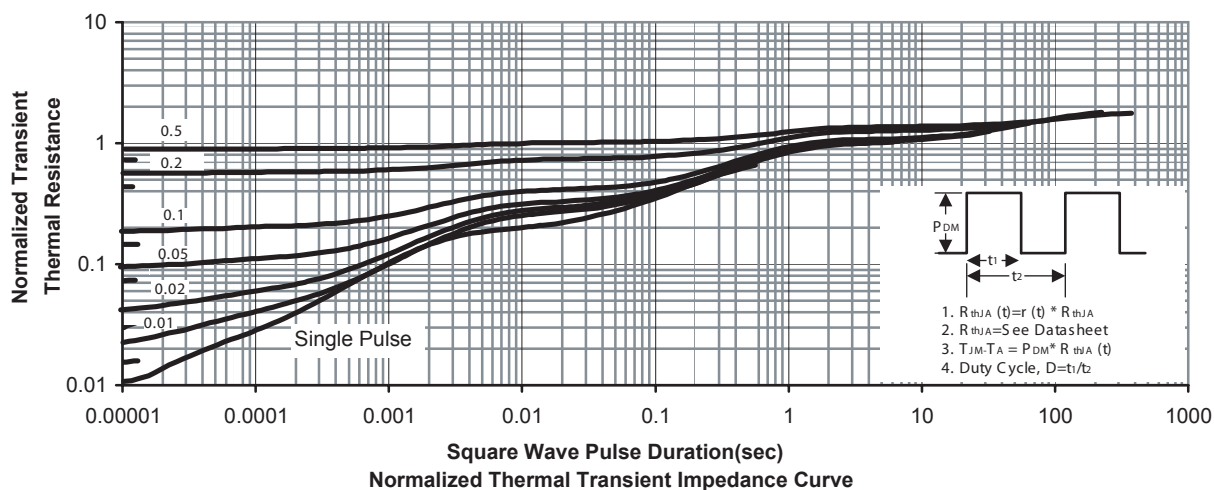


Figure 12. Switching Waveforms

N-Channel



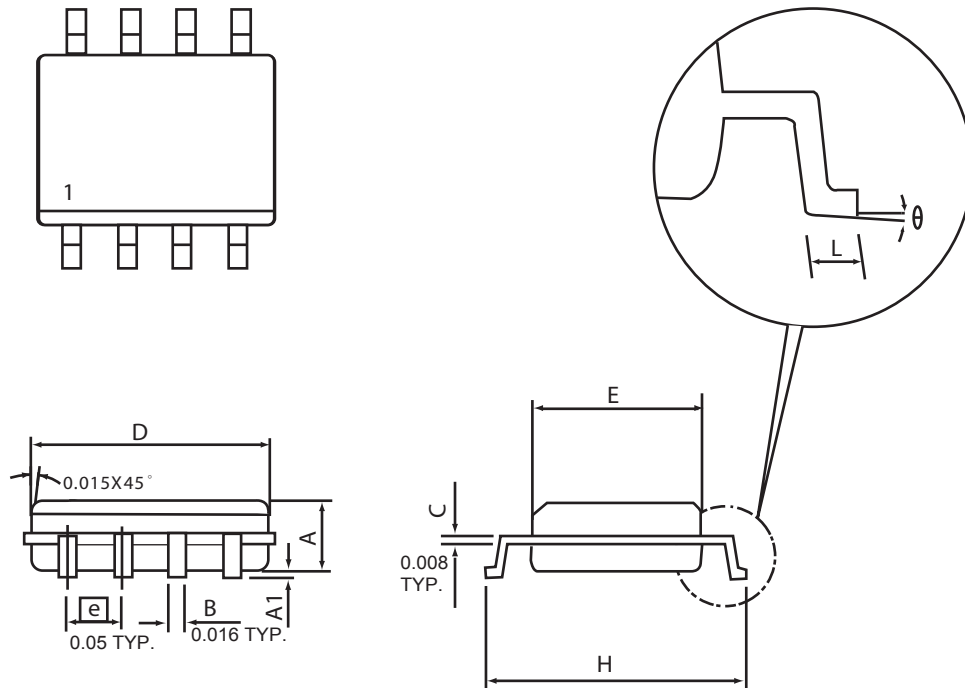
P-Channel



STM8450

PACKAGE OUTLINE DIMENSIONS

SO-8

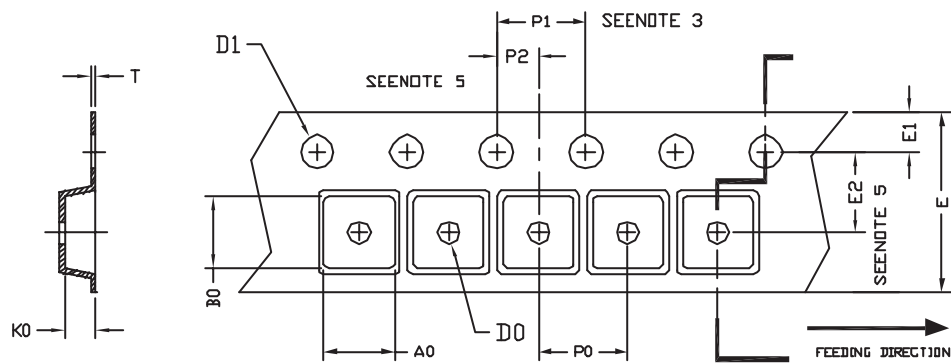


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

STM8450

SO-8 Tape and Reel Data

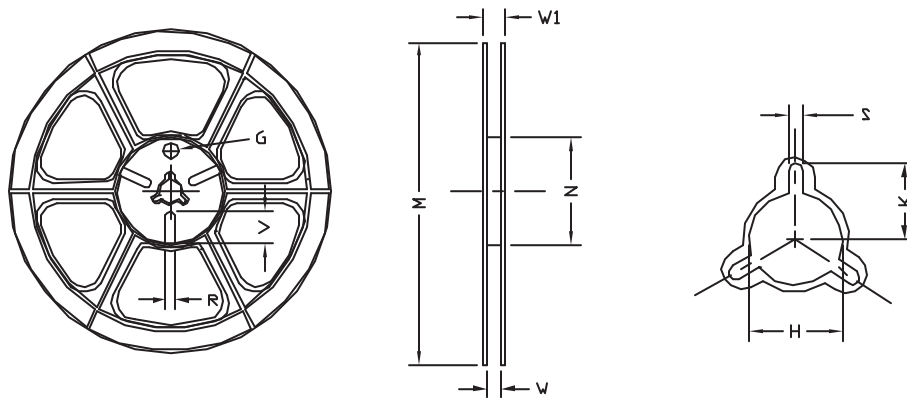
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 ± 0.15	---	---	---